

NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

Units Symbol Parameter Value Collector-Emitter Voltage 50 VCEO V V V_{CBO} Collector-Base Voltage 50 Emitter-Base Voltage 5.0 V V_{EBO} Collector Current - Continuous 500 mΑ I_{C} T_J, T_{stg} Operating and Storage Junction Temperature Range -55 to +150 °C

TA = 25°C unless otherwise noted

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

| Symbol | Characteristic | Max | Units | |
|---------------------|---|-----------------|-------|--|
| | | 2N3416 / 2N3417 | _ | |
| PD | Total Device Dissipation | 625 | mW | |
| | Derate above 25°C | 5.0 | mW/°C | |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 83.3 | °C/W | |
| $R_{	ext{	heta}JA}$ | Thermal Resistance, Junction to Ambient | 200 | °C/W | |

TA = 25°C unless otherwise noted

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NPN General Purpose Amplifier (continued)

| Electrical Characteristics TA = 25°C unless otherwise noted | | | | | | |
|---|---|---|-----|-----------|----------|--|
| Symbol | Parameter | Test Conditions | Min | Max | Units | |
| OFF CHA | RACTERISTICS | | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | I _C = 10 mA, I _B = 0 | 50 | | V | |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$ | 50 | | V | |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_{E} = 10 \ \mu A, \ I_{C} = 0$ | 5.0 | | V | |
| I _{CBO} | Collector-Cutoff Current | $V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 18 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ | | 100 15 | nA μA | |
| I _{EBO} | Emitter-Cutoff Current | $V_{EB} = 5.0 \text{ V}, I_{C} = 0$ | | 100 | nA | |

ON CHARACTERISTICS*

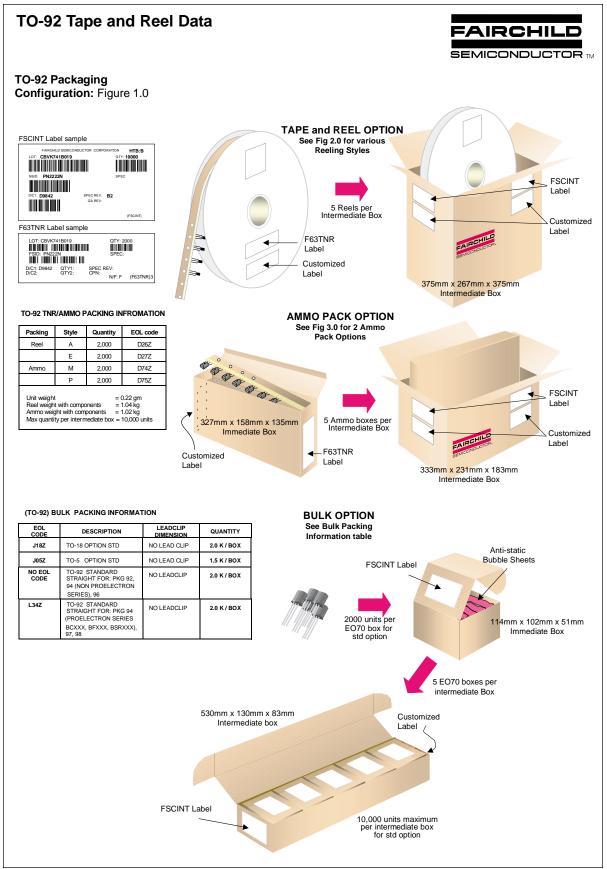
| h _{FE} | DC Current Gain | $V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$ | | | |
|----------------------|--------------------------------------|--|-----|-----|---|
| | | 2N3416 | 75 | 225 | |
| | | 2N3417 | 180 | 540 | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{C} = 50 \text{ mA}, I_{B} = 3.0 \text{ mA}$ | | 0.3 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | $I_{C} = 50 \text{ mA}, I_{B} = 3.0 \text{ mA}$ | 0.6 | 1.3 | V |

SMALL SIGNAL CHARACTERISTICS

| h _{fe} | Small-Signal Current Gain | $I_{\rm C} = 2.0 \text{ mA}, V_{\rm CE}$ | $I_{C} = 2.0 \text{ mA}, V_{CE} = 4.5 \text{ V},$ | | |
|-----------------|---------------------------|--|---|-----|--|
| | | f = 1.0 kHz | 2N3416 | 75 | |
| | | | 2N3417 | 180 | |

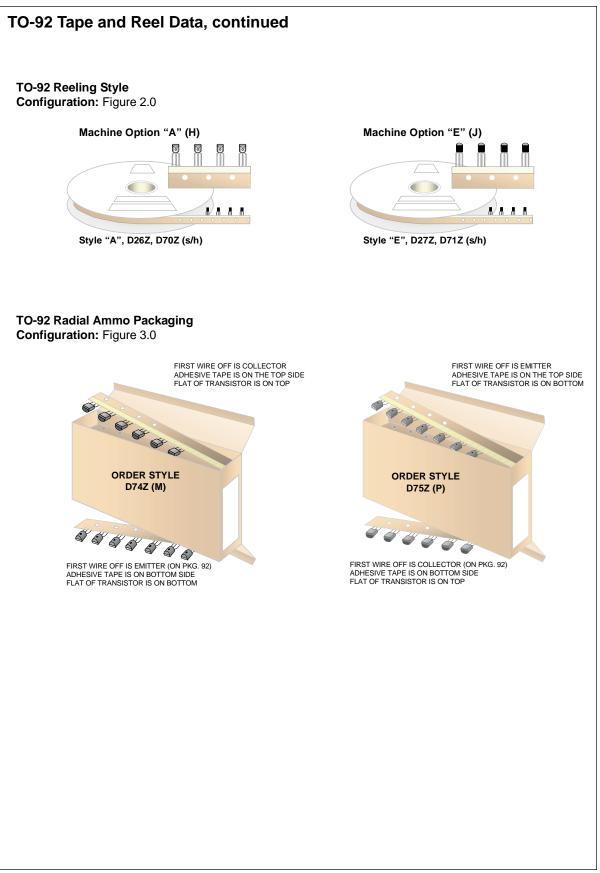
*Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

2N3416 / 2N3417



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PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|---------------------------|---|
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